



Diode Modules MDx-320-28-C1



Average forward current		I_{FAV}		320 A	
Repetitive peak reverse voltage		V_{RRM}		2000...2800 V	
V_{RRM}, V	2000	2200	2400	2600	2800
Voltage code	20	22	24	26	28
$T_j, ^\circ C$	-40...+150				

MD3	MD4	MD5

MAXIMUM ALLOWABLE RATINGS

Symbols and parameters		Units	Values	Test conditions	
ON-STATE					
I_{FAV}	Maximum allowable average forward current	A	320 428	$T_c = 116\text{ °C}$; $T_c = 100\text{ °C}$; 180° half-sine wave; 50 Hz	
I_{FRMS}	RMS forward current	A	502	$T_c = 116\text{ °C}$; 180° half-sine wave; 50 Hz	
I_{FSM}	Surge forward current	kA	8.5 10.0	$T_j = T_{j\max}$ $T_j = 25\text{ °C}$	180° half-sine wave; $t_p = 10\text{ ms}$; single pulse; $V_R = 0\text{ V}$;
			9.0 10.5	$T_j = T_{j\max}$ $T_j = 25\text{ °C}$	180° half-sine wave; $t_p = 8.3\text{ ms}$; single pulse; $V_R = 0\text{ V}$;
I^2t	Safety factor	$A^2s \cdot 10^3$	360 500	$T_j = T_{j\max}$ $T_j = 25\text{ °C}$	180° half-sine wave; $t_p = 10\text{ ms}$; single pulse; $V_R = 0\text{ V}$;
			330 450	$T_j = T_{j\max}$ $T_j = 25\text{ °C}$	180° half-sine wave; $t_p = 8.3\text{ ms}$; single pulse; $V_R = 0\text{ V}$;
BLOCKING					
V_{RRM}	Repetitive peak reverse voltages	V	2000...2800	$T_{j\min} < T_j < T_{j\max}$; 180° half-sine wave; 50 Hz;	
V_{RSM}	Non-repetitive peak reverse voltages	V	2100...2900	$T_{j\min} < T_j < T_{j\max}$; 180° half-sine wave; single pulse;	
V_R	Reverse continuous voltages	V	$0.6 \cdot V_{RRM}$	$T_j = T_{j\max}$;	
THERMAL					
T_{stg}	Storage temperature	°C	-40...+50		
T_j	Operating junction temperature	°C	-40...+150		
$T_{c\ op}$	Operating temperature	°C	-40...+125		
MECHANICAL					
a	Acceleration under vibration	m/s^2	50		

CHARACTERISTICS

Symbols and parameters		Units	Values	Conditions	
ON-STATE					
V_{FM}	Peak forward voltage, max	V	1.40	$T_j = 25\text{ °C}$; $I_{FM} = 785\text{ A}$	
$V_{F(TO)}$	Forward threshold voltage, max	V	0.937	$T_j = T_{j\max}$;	
r_T	Forward slope resistance, max	$m\Omega$	0.495	$0.5 \pi I_{FAV} < I_T < 1.5 \pi I_{FAV}$	
BLOCKING					
I_{RRM}	Repetitive peak reverse current, max	mA	30 2.50	$T_j = T_{j\max}$ $T_j = 25\text{ °C}$	$V_R = V_{RRM}$
SWITCHING					
Q_r	Recovered charge, max	μC	2160	$T_j = T_{j\max}$; $I_{FM} = I_{FAV}$;	
t_{rr}	Reverse recovery time, max	μs	31	$di_R/dt = -10\text{ A}/\mu s$;	
I_{rr}	Reverse recovery current, max	A	139	$V_R = 100\text{ V}$;	
THERMAL					
R_{thjc}	Thermal resistance, junction to case			180° half-sine wave, 50 Hz	
	per module	°C/W	0.0400		
	per arm	°C/W	0.0800		
R_{thch}	Thermal resistance, case to heatsink				
	per module	°C/W	0.0200		
	per arm	°C/W	0.0400		

INSULATION					
V _{ISOL}	Insulation test voltage	kV	3.00	Sine wave, 50 Hz; RMS	t=60 sec
			3.60		t=1 sec
MECHANICAL					
M ₁	Mounting torque (M6) ¹⁾	Nm	6.00	Tolerance ± 15%	
M ₂	Terminal connection torque (M8) ¹⁾	Nm	9.00	Tolerance ± 15%	
m	Weight, max	g	860		

PART NUMBERING GUIDE						NOTES				
MD	3	-	320	-	28	-	C1	-	N	¹⁾ The screws must be lubricated
	1	2	3	4	5	6				
1. MD - Rectifier Diode 2. Circuit Schematic 3. Average Forward Current, A 4. Voltage Code 5. Package Type (M.C1) 6. Ambient Conditions: N – Normal										

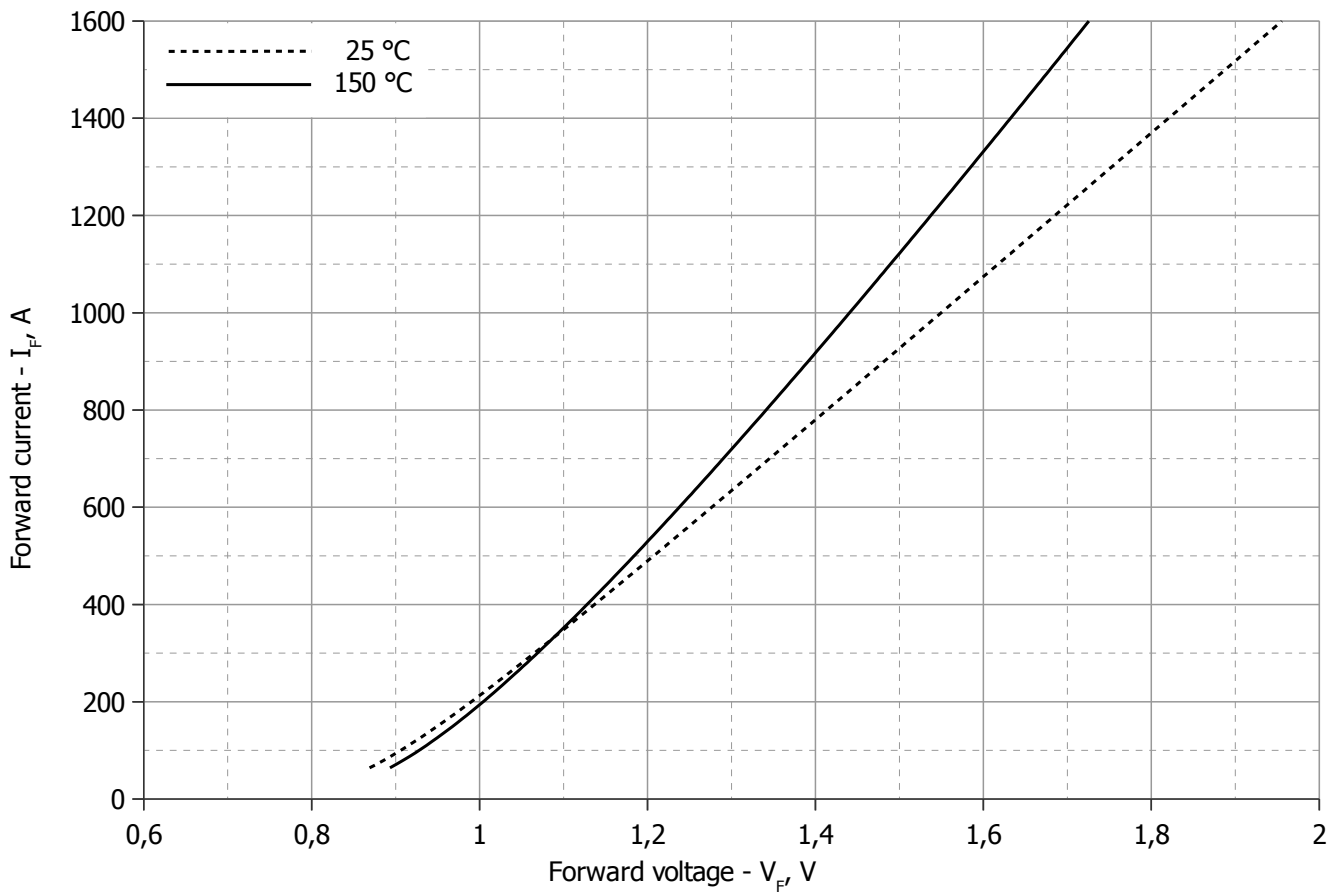


Fig 1 – Forward characteristics of Limit device

Analytical function for Forward characteristic:

$$U_F = A + B \cdot i_F + C \cdot \ln(i_F + 1) + D \cdot \sqrt{i_F}$$

	Коэффициенты для графика	
	$T_j = 25^\circ\text{C}$	$T_j = T_{j \max}$
A	0.66691207	0.72796686
B	0.00069885	0.00038313
C	0.04567533	0.02361196
D	-0.00416396	0.00526168

Forward characteristic model (see Fig. 1).

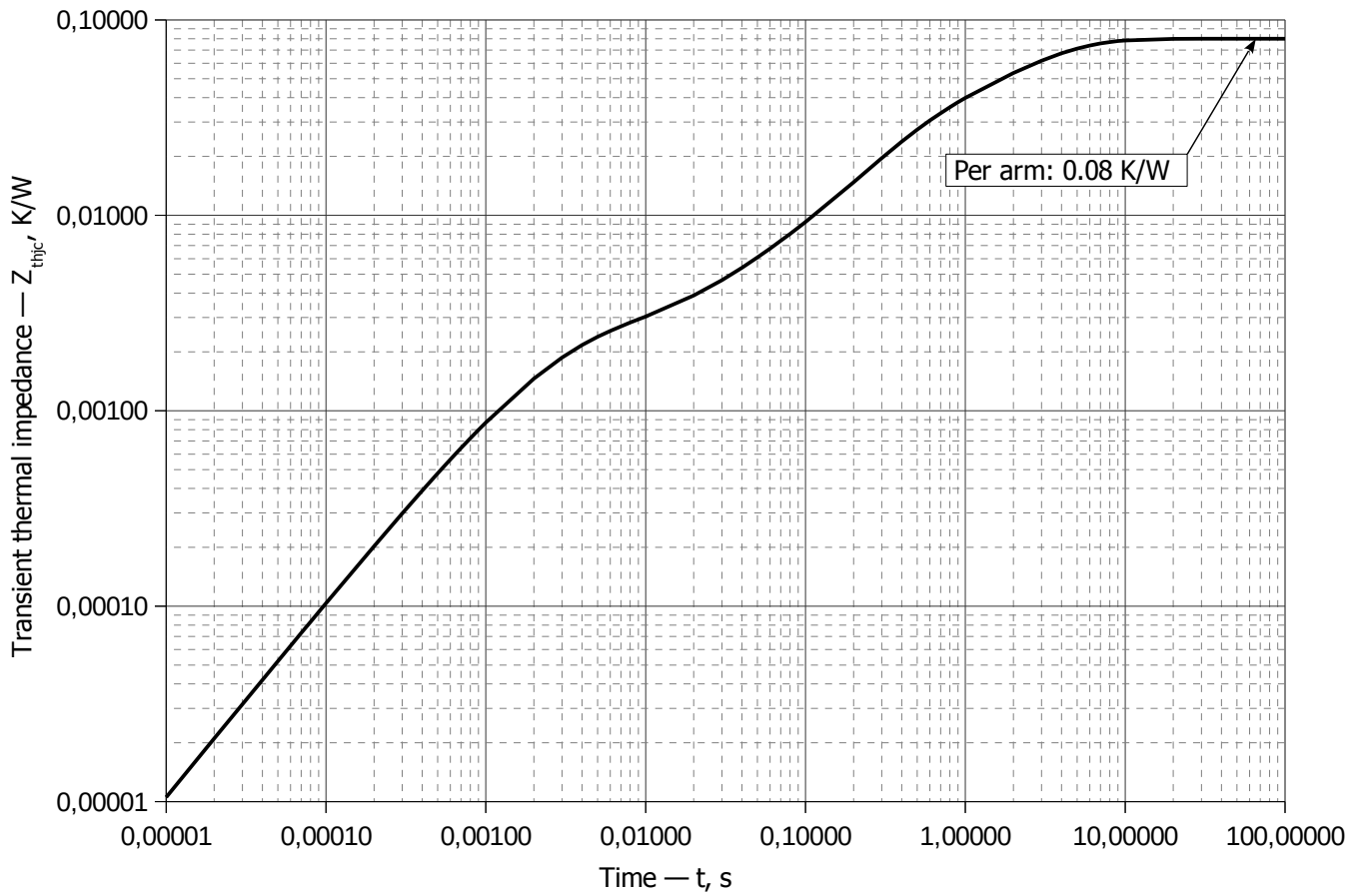


Fig 2 – Transient thermal impedance Z_{thjc} vs. time t

Analytical function for Transient thermal impedance junction to case Z_{thjc} for DC:

$$Z_{thjc} = \sum_{i=1}^n R_i \left(1 - e^{-\frac{t}{\tau_i}} \right)$$

Where $i = 1$ to n , n is the number of terms in the series.

t = Duration of heating pulse in seconds.

Z_{thjc} = Thermal resistance at time t .

R_i = Amplitude of p_{th} term.

τ_i = Time constant of r_{th} term.

DC

i	1	2	3	4	5	6
R_i , K/W	0.0507	0.007806	0.02226	-0.007688	0.00471	0.00217
τ_i , s	2.801	1.283	0.3281	0.09408	0.0572	0.002255

Transient thermal impedance junction to case Z_{thjc} model (see Fig. 2)

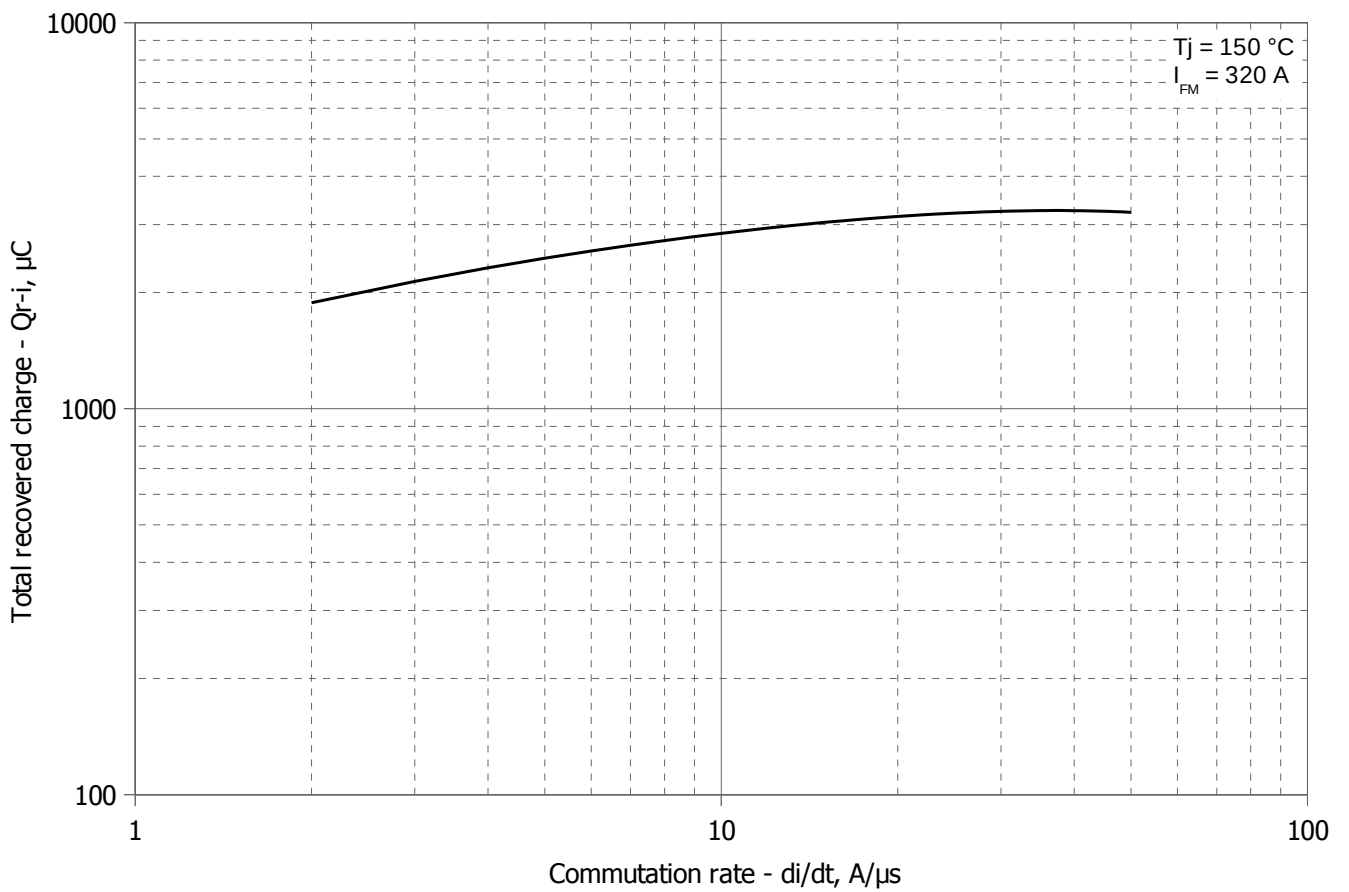


Fig 3 – Maximum recovered charge Q_{r-i} (integral) vs. commutation rate di_R/dt

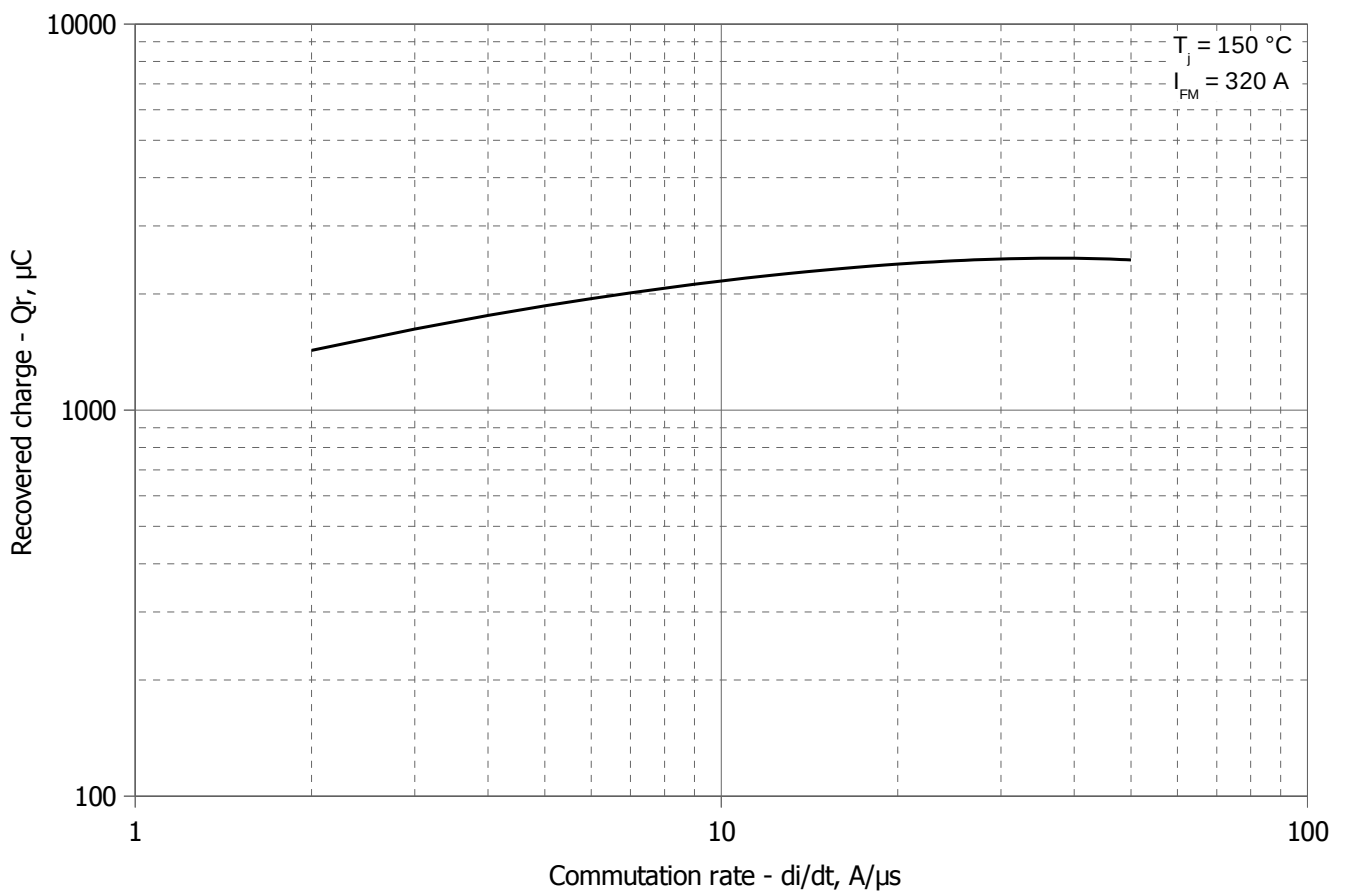


Fig 4 – Maximum recovered charge Q_r vs. commutation rate di_R/dt (25% chord)

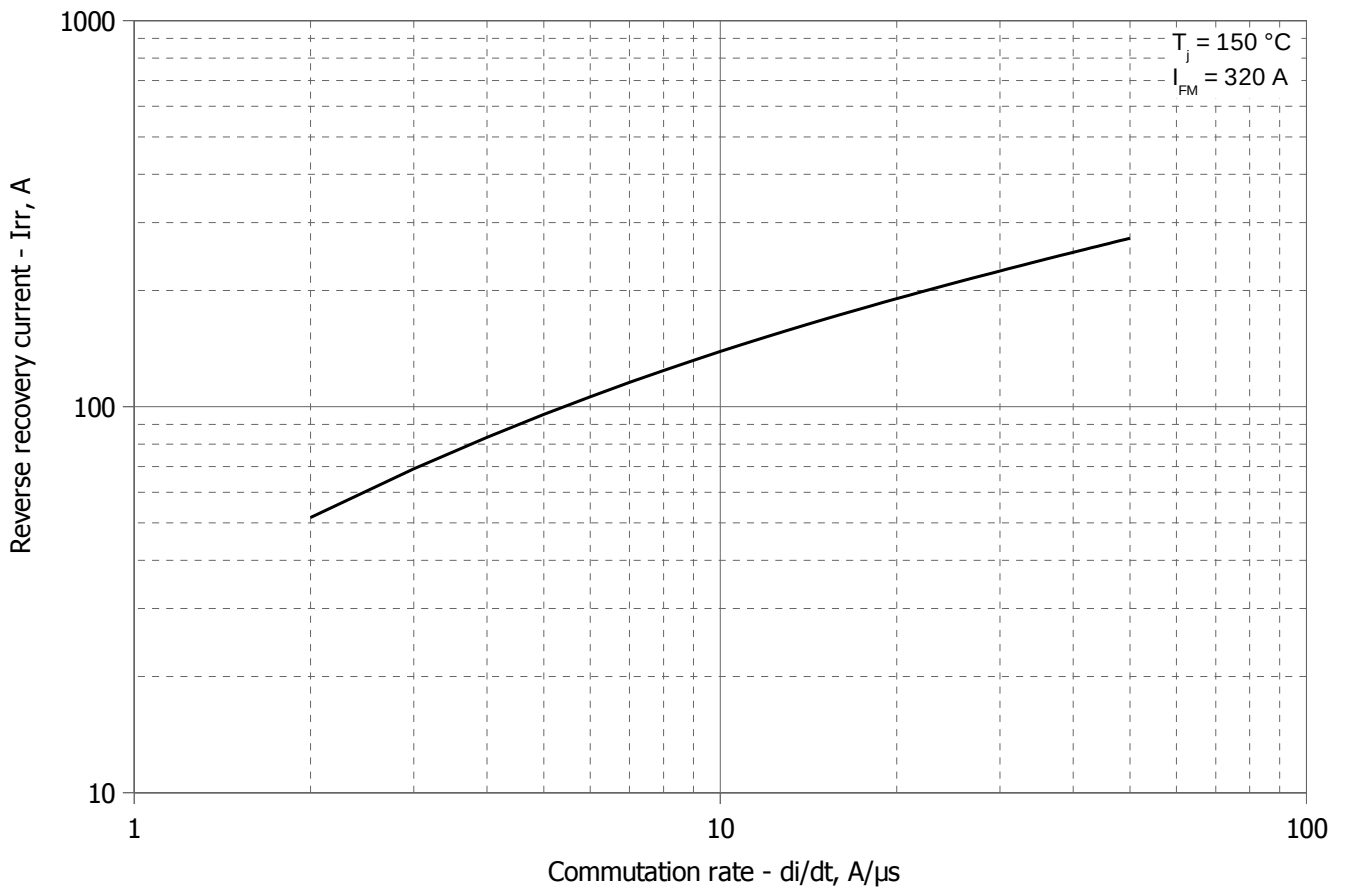


Fig 5 – Maximum reverse recovery current I_{rr} vs. commutation rate di_R/dt

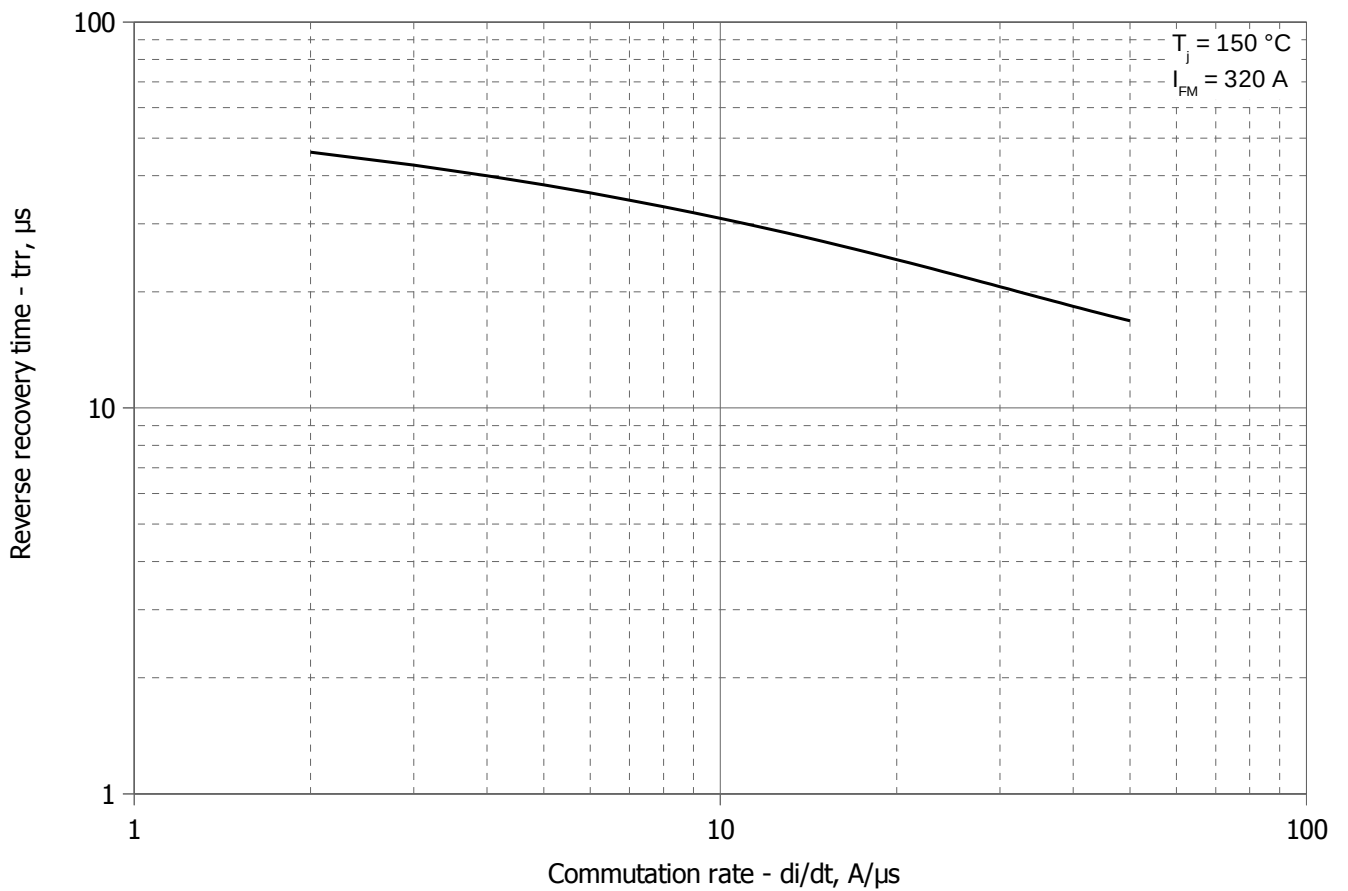


Fig 6 – Maximum recovery time t_{rr} vs. commutation rate di_R/dt (25% chord)

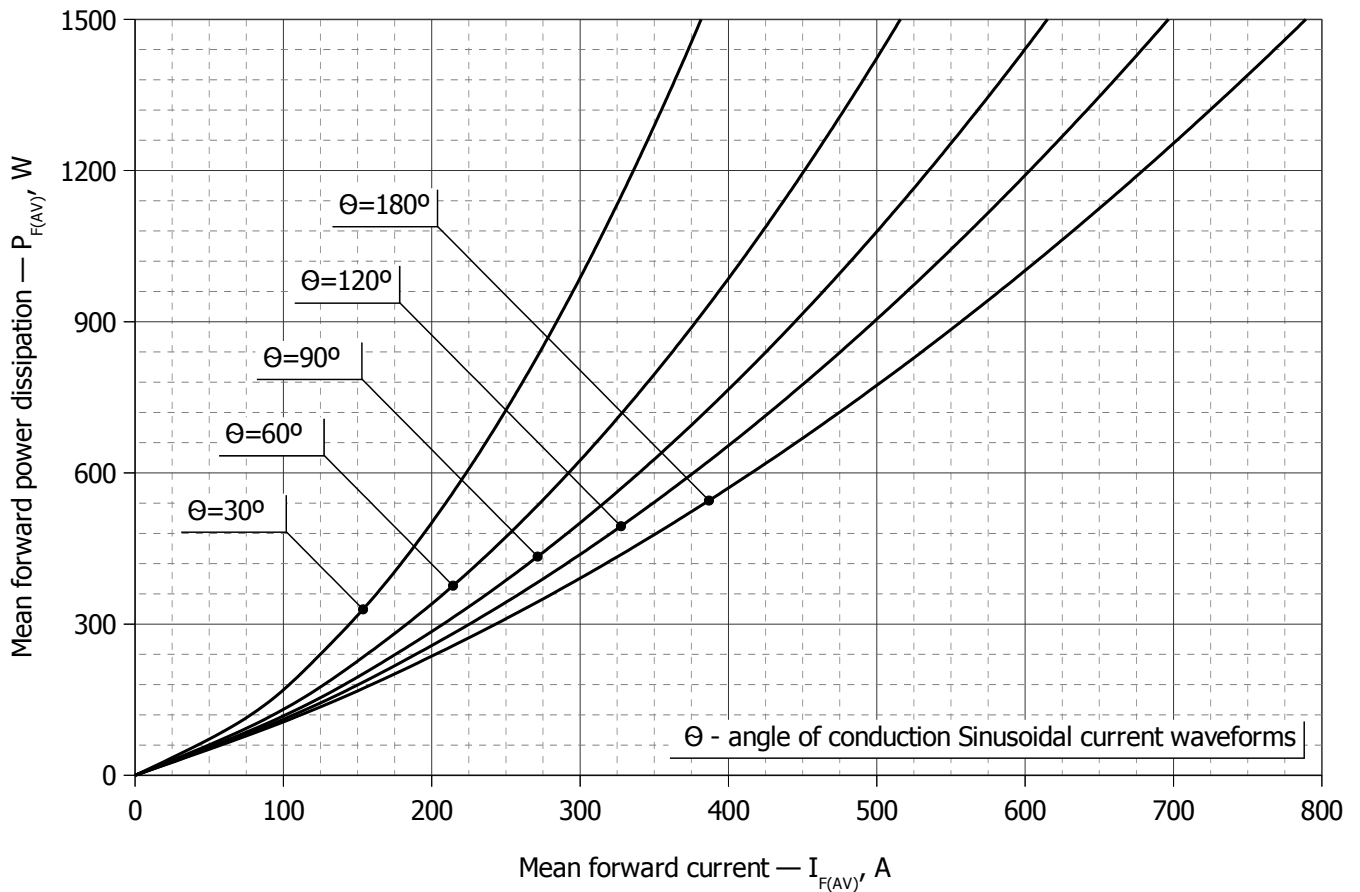


Fig. 7 - Mean forward power dissipation P_{FAV} vs. mean forward current I_{FAV} for sinusoidal current waveforms at different conduction angles ($f=50\text{Hz}$)

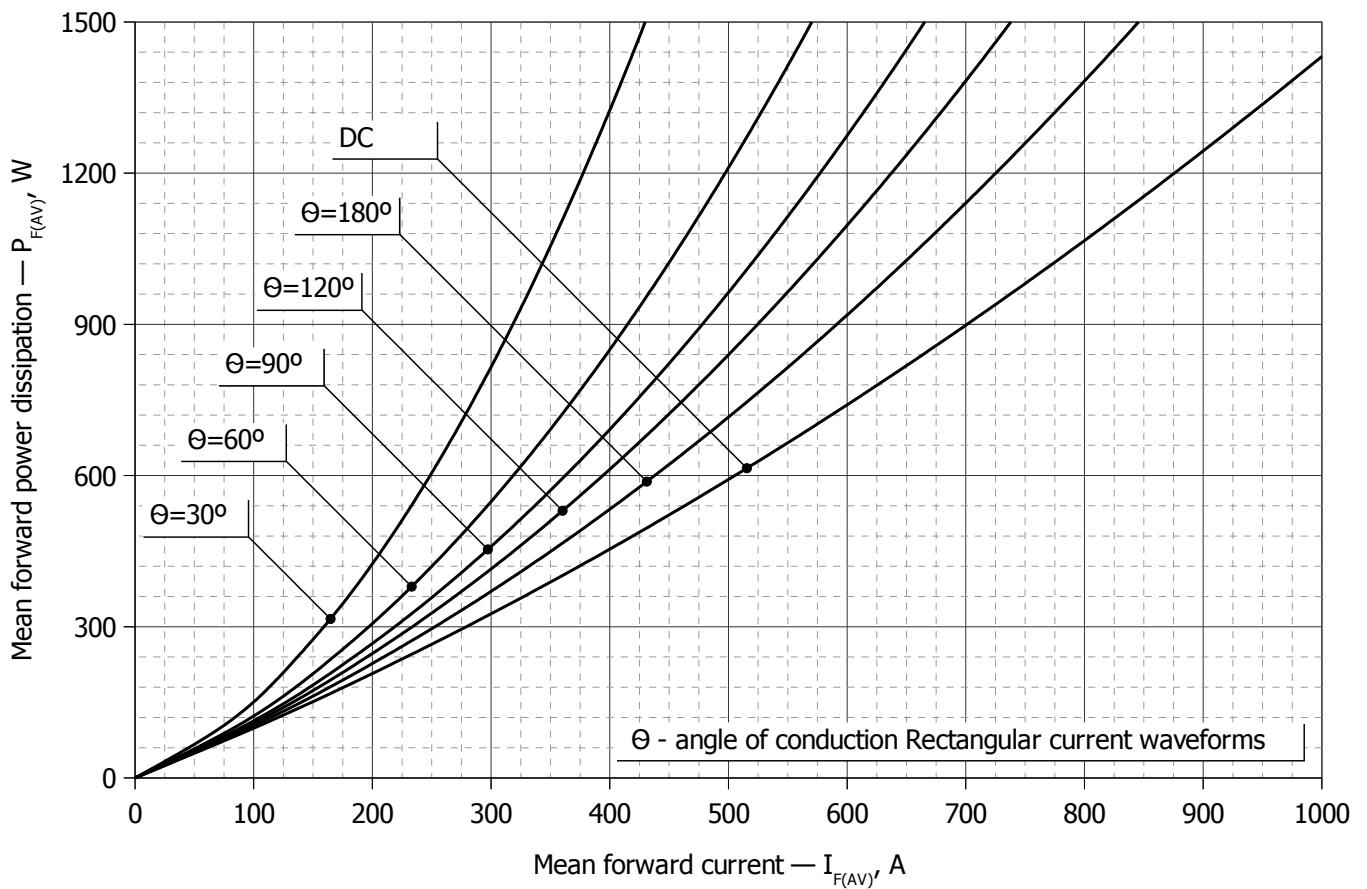


Fig. 8 - Mean forward power dissipation P_{FAV} vs. mean forward current I_{FAV} for rectangular current waveforms at different conduction angles and for DC ($f=50\text{Hz}$)

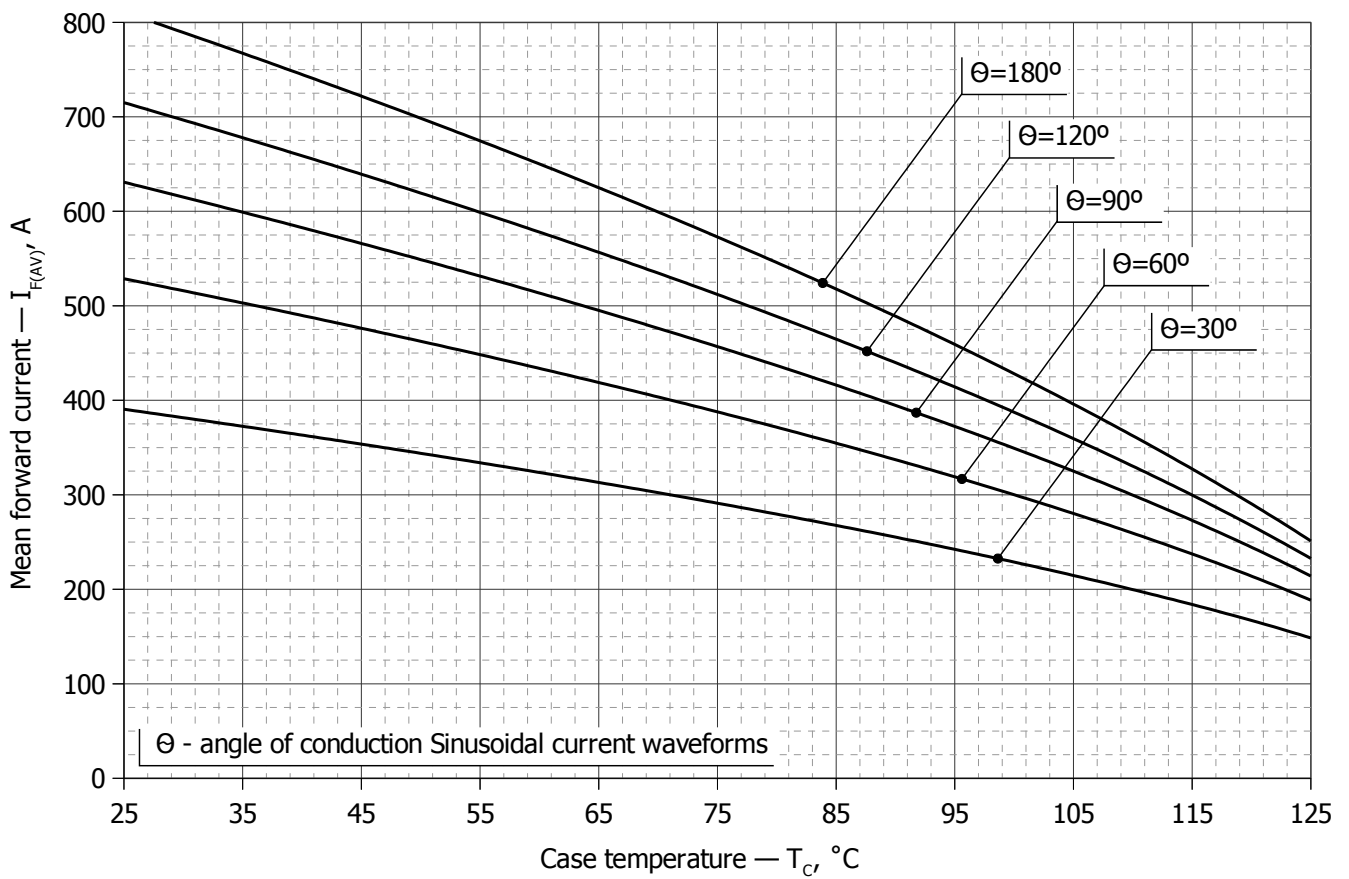


Fig. 9 – Mean forward current I_{FAV} vs. case temperature T_C for sinusoidal current waveforms at different conduction angles ($f=50Hz$)

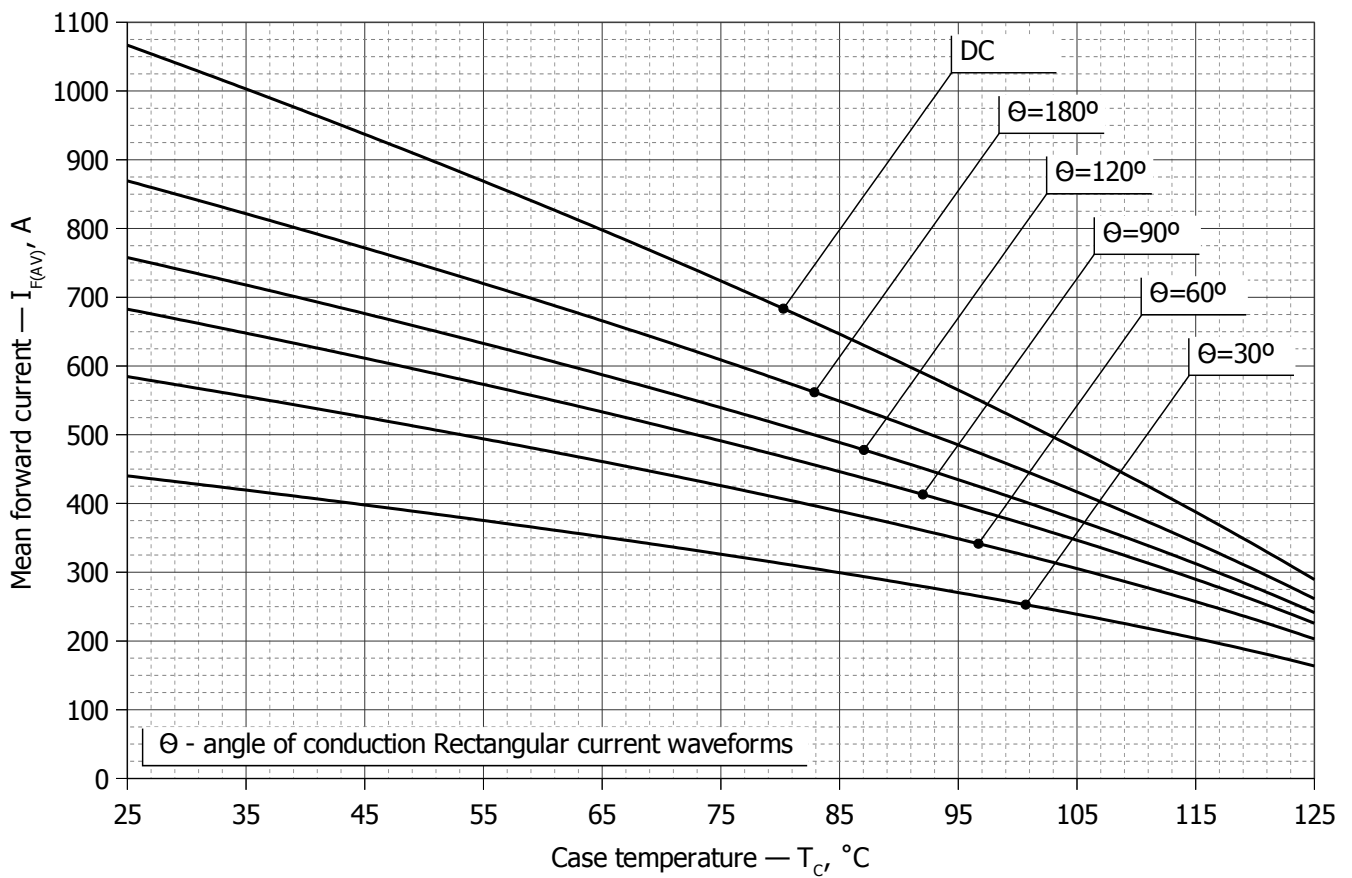


Fig. 10 - Mean forward current I_{FAV} vs. case temperature T_C for rectangular current waveforms at different conduction angles and for DC ($f=50Hz$)

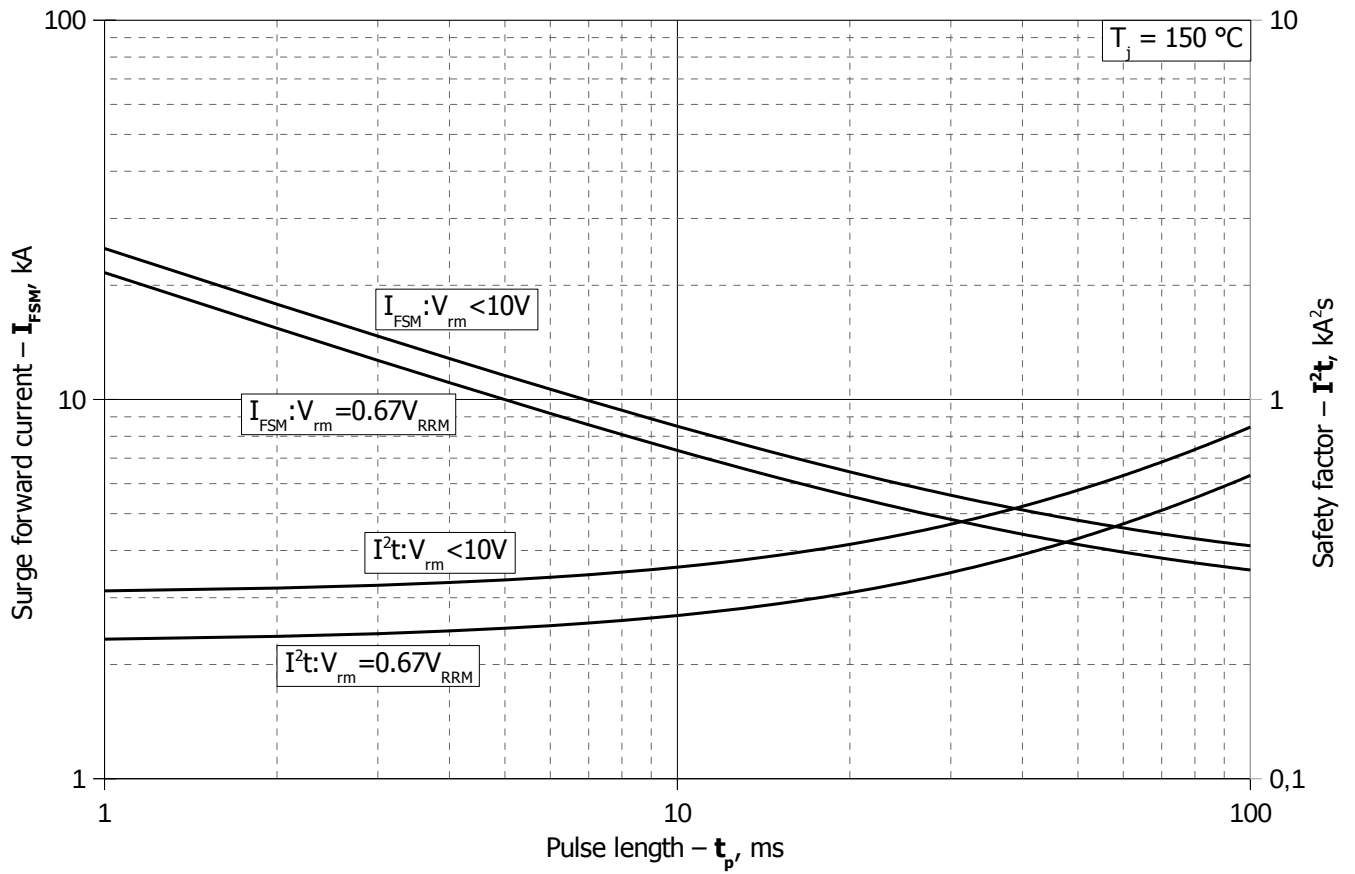


Fig. 11 – Maximum surge forward current I_{FSM} and safety factor I^2t vs. pulse length t_p

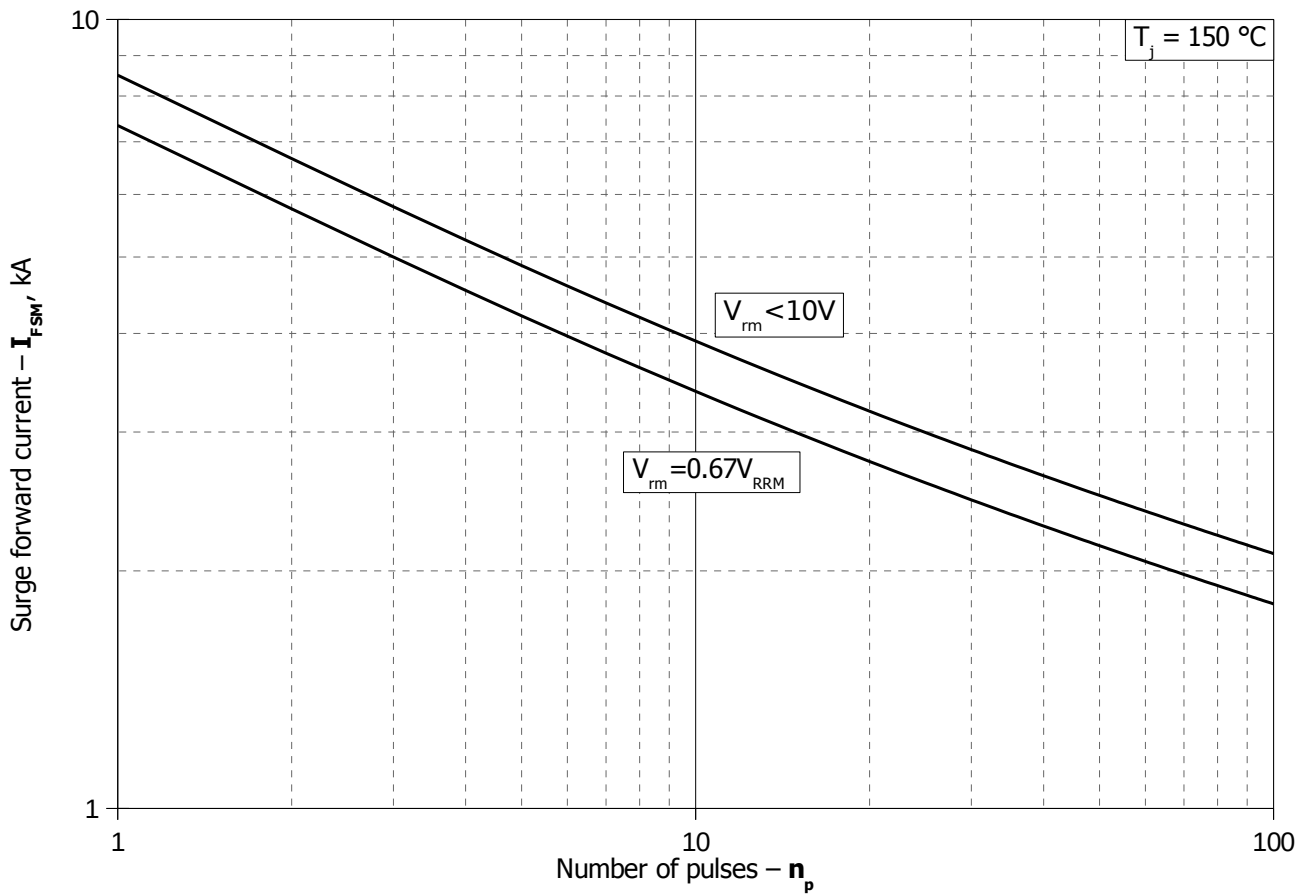


Fig. 12 - Maximum surge forward current I_{FSM} vs. number of pulses n_p